

Medium power transistor (32V, 2A)

2SD1766 / 2SD1758 / 2SD1862

Features

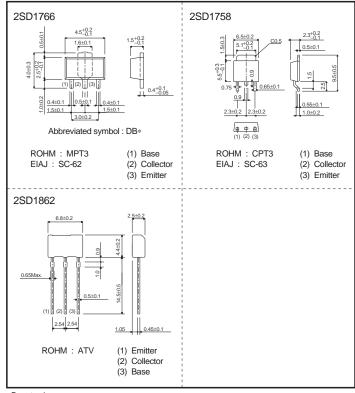
1) Low VCE(sat). $V_{CE(sat)} = 0.5V (Typ.)$ $(Ic/I_B = 2A / 0.2A)$

2) Complements the 2SB1188 / 2SB1182 / 2SB1240

Structure

Epitaxial planar type NPN silicon transistor

●Dimensions (Unit: mm)



* Denotes hre

●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit	
Collector-base voltage		Vсво	40	V	
Collector-emitter voltage		Vceo	32	V	
Emitter-base voltage		V _{ЕВО}	5	V	
Collector current		Ic	2	A (DC)	
			2.5 *1	A (Pulse)	
Collector power dissipation	2SD1766		0.5	W	
		Pc	2 *2		
	2SD1758	PC	10	W (Tc=25°C)	
	2SD1862		1 *3	W	
Junction temperature		Tj	150	°C	
Storage temperature		Tstg	-55~+150	°C	

^{*1} Single pulse, Pw=20ms

^{*2} When mounted on a 40×40×0.7 mm ceramic board. *3 Printed circuit board: 1.7 mm thick, collector copper plating 1 cm² or lager.

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Collector-base breakdown voltage	ВУсво	40	_	_	V	Ic=50μA	
Collector-emitter breakdown voltage	BVceo	32	_	_	V	Ic=1mA	
Emitter-base breakdown voltage	ВУЕВО	5	_	_	V	Iε=50μA	
Collector cutoff current	Ісво	_	_	1	μА	Vcb=20V	
Emitter cutoff current	ІЕВО	_	_	1	μΑ	V _{EB} =4V	
DC current transfer ratio	hfe	120	_	390	_	Vce=3V, Ic=0.5A	*
Collector-emitter saturation voltage	VCE(sat)	_	0.5	0.8	V	Ic/I _B =2A / 0.2A	*
Transition frequency	f⊤	_	100	_	MHz	Vce=5V, Ie=-50mA, f=100MHz	*
Output capacitance	Cob	_	30	-	pF	Vcb=10V, Ie=0A, f=1MHz	

^{*} Measured using pulse current.

●Packaging specifications and hFE

		Package	Taping		
		Code	T100	TL	TV2
Туре	hfe	Basic ordering unit (pieces)	1000	2500	2500
2SD1766	QR		0	-	-
2SD1758	QR		_	0	_
2SD1862	QR		-	-	0

hre values are classified as follows:

Item	Q	R	
hfe	120 to 270	180 to 390	

• Electrical characteristic curves

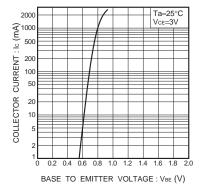


Fig.1 Grounded emitter propagation characteristics

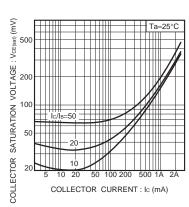


Fig.4 Collector-emitter saturation voltage vs. collector current

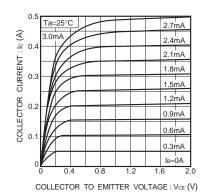


Fig.2 Grounded emitter output characteristics

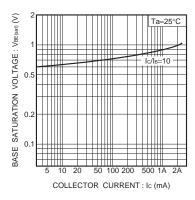


Fig.5 Collector-emitter saturation voltage vs. collector current

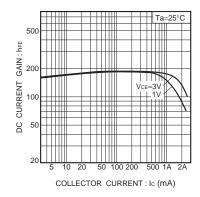


Fig.3 DC current gain vs. collector

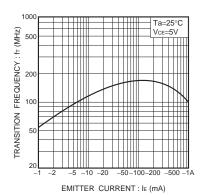


Fig.6 Transition frequency vs. emitter current

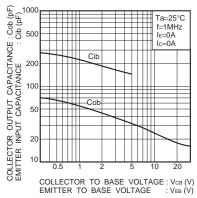


Fig.7 Collector output capacitance vs. collector-base voltage Emitter input capacitance vs. emitter-base voltage

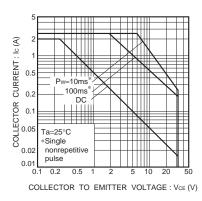


Fig.8 Safe operating area (2SD1766)

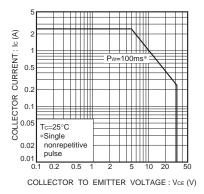
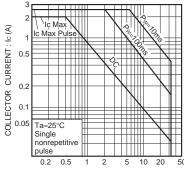


Fig.9 Safe operating area (2SD1758)



COLLECTOR TO EMITTER VOLTAGE: VCE (V)

Fig.10 Safe operating area (2SD1862)

Notes

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